

SCT2280KE N-channel SiC power MOSFET

V _{DSS}	1200V
R _{DS(on)} (Typ.)	280mΩ
ا _D	14A
P _D	108W

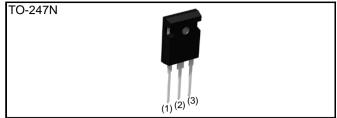
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

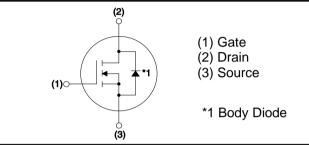
Application

- Solar inverters
- DC/DC converters
- Induction heating
- Motor drives

Outline



Inner circuit



Packaging specifications

Package		TO-247N
Packing		Tube
Reel size	Reel size (mm)	-
Tuno	Tape width (mm)	-
Type Basic	Basic ordering unit (pcs)	30
	Packing code	C11
	Marking	SCT2280KE

●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V _{DSS}	1200	V
$T_c = 25^{\circ}C$		I _D ^{*1}	14	А
Continuous drain current	$T_c = 100^{\circ}C$	ا _D *1	10	А
Pulsed drain current		I _{D,pulse} *2	35	А
Gate - Source voltage (DC)		V _{GSS}	-6 to 22	V
Gate - Source surge voltage (T _{surge} < 300nsec)		V _{GSS-surge} *3	-10 to 26	V
Power dissipation $(T_c = 25^{\circ}C)$		P _D	108	W
Junction temperature		Tj	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

•Electrical characteristics ($T_a = 25^{\circ}C$)

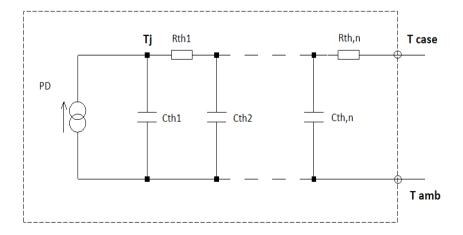
Parameter	Sumbol	bol Conditions -		Values		
Farameter	Symbol			Тур.	Max.	Unit
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V, I_D = 1mA$	1200	-	-	V
		$V_{DS} = 1200V, V_{GS} = 0V$				
Zero gate voltage drain current	I _{DSS}	$T_j = 25^{\circ}C$	-	1	10	μA
		T _j = 150°C	-	2	-	
Gate - Source leakage current	I_{GSS^+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}, I_D = 1.4 \text{mA}$	1.6	2.8	4.0	V

Thermal resistance

Parameter	Symbol	Values			Unit	
Faranielei	Symbol	Min.	Тур.	Max.	Offic	
Thermal resistance, junction - case	R _{thJC}	-	1.07	1.39	°C/W	
Thermal resistance, junction - ambient	R _{thJA}	-	-	50	°C/W	
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C	

•Typical Transient Thermal Characteristics

Symbol	Value	Unit	Symbol	Value	Unit
R _{th1}	1.00E-01		C _{th1}	8.61E-04	
R _{th2}	6.62E-01	K/W	C _{th2}	2.84E-03	Ws/K
R _{th3}	3.04E-01		C_{th3}	5.59E-02	<u> </u>





•Electrical characteristics ($T_a = 25^{\circ}C$)

Deremeter	Cumhal	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS} = 18V$, $I_D = 4A$				
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	T _j = 25°C	-	280	364	mΩ
		T _j = 125°C	-	388	-	
Gate input resistance	R _G	f = 1MHz, open drain	-	17	-	Ω
Transconductance	g _{fs} *4	$V_{DS} = 10V, I_D = 4A$	-	1.4	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	667	-	
Output capacitance	C _{oss}	V _{DS} = 800V	-	27	-	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	5	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	41	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 400 V, V_{GS} = 18 V$	-	19	-	
Rise time	t _r *4	$I_D = 4A$	-	19	-	
Turn - off delay time	t _{d(off)} *4	R _L = 100Ω	-	47	-	ns
Fall time	t _f *4	$R_{G} = 0\Omega$	-	29	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 600V, I_{D} = 4A$ $V_{GS} = 18V/0V$	-	57	-	
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=500μH *E _{on} includes diode reverse recovery	-	20	-	μJ

•Gate Charge characteristics ($T_a = 25^{\circ}C$)

Parameter	Symbol	Conditions		Unit		
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Q_g^{*4}	V _{DD} = 400V	-	36	-	
Gate - Source charge	Q _{gs} ^{*4}	$I_D = 4A$	-	9	-	nC
Gate - Drain charge	Q_{gd}^{*4}	V _{GS} = 18V	-	12	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 400V, I_D = 4A$	-	9.8	-	V

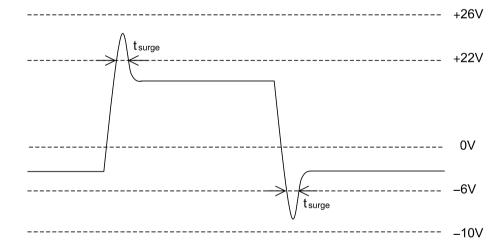


●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Sumbol	Conditions		Unit			
Faranielei	Symbol Conditions –		Min.	Тур.	Max.	Unit	
Inverse diode continuous, forward current	ا _S *1	T _c = 25°C	-	-	14	А	
Inverse diode direct current, pulsed	I _{SM} *2		-	-	35	А	
Forward voltage	V_{SD} *4	$V_{GS} = 0V, I_S = 4A$	-	4.0	-	V	
Reverse recovery time	t _{rr} *4		-	22	-	ns	
Reverse recovery charge		I _F = 4A, V _R = 400V di/dt = 160A/μs	-	21	-	nC	
Peak reverse recovery current	^{*4}	*4		2.0	-	А	

*1 Limited only by maximum temperature allowed.

- *2 PW \leq 10µs, Duty cycle \leq 1%
- *3 Example of acceptable V_{GS} waveform



*4 Pulsed



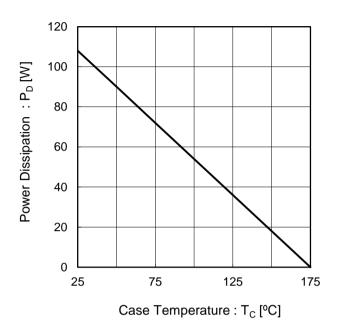


Fig.1 Power Dissipation Derating Curve

Fig.2 Maximum Safe Operating Area

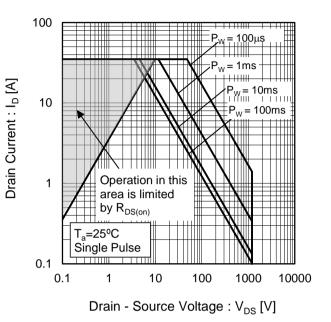
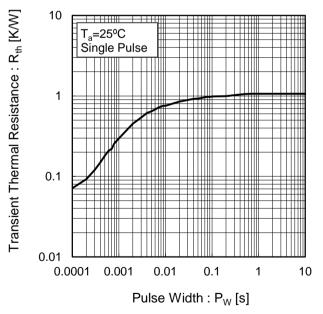


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



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12V

10V

2V

10V

5

5

Electrical characteristic curves

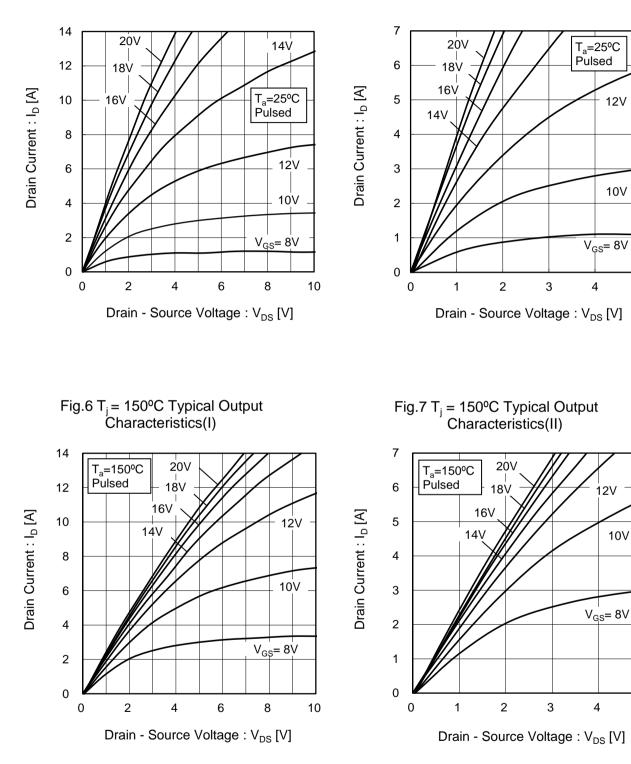


Fig.4 Typical Output Characteristics(I)

Fig.5 Typical Output Characteristics(II)



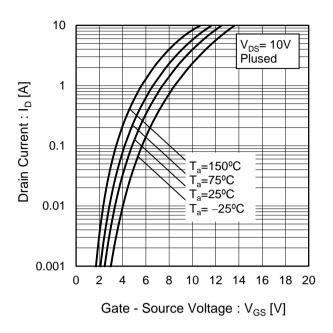


Fig.8 Typical Transfer Characteristics (I)

Fig.9 Typical Transfer Characteristics (II)

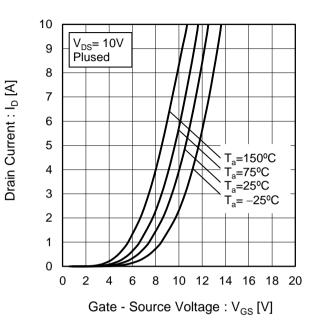
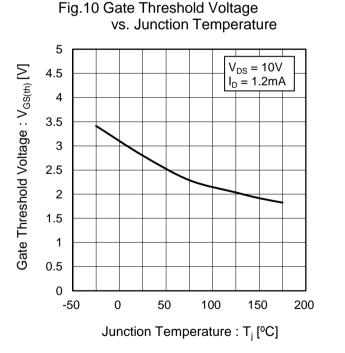
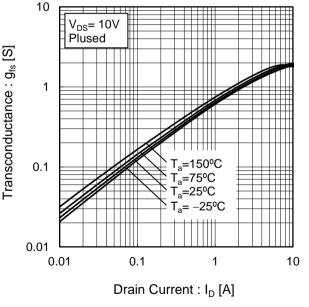


Fig.11 Transconductance vs. Drain Current







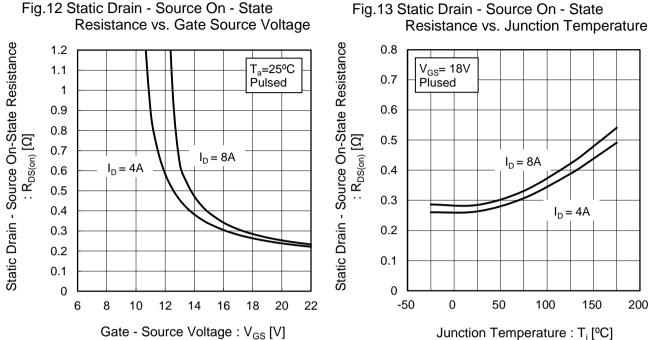


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current

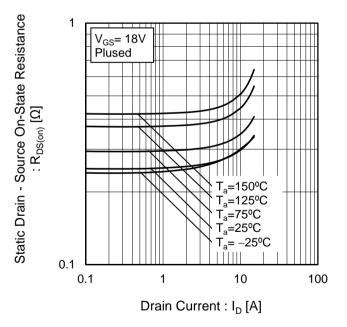


Fig.13 Static Drain - Source On - State



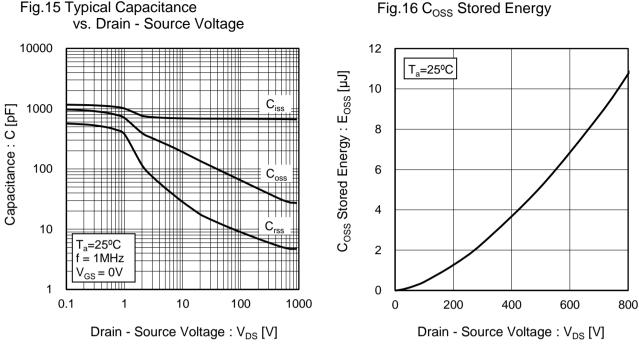
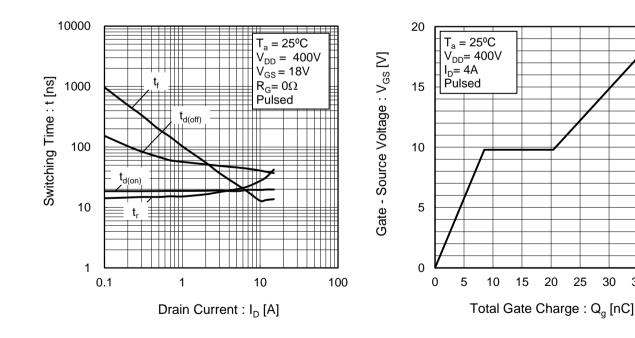


Fig.15 Typical Capacitance

Fig.17 Switching Characteristics

Fig.18 Dynamic Input Characteristics





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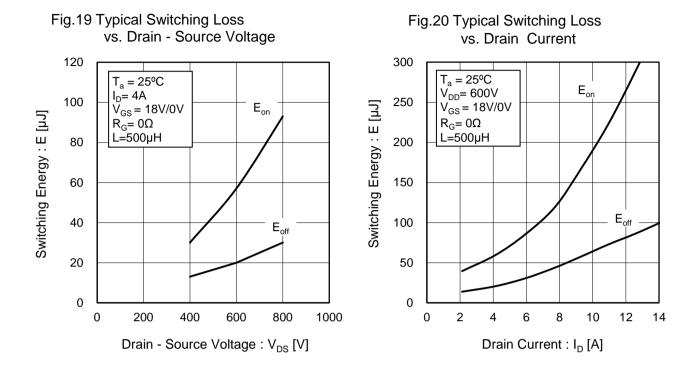
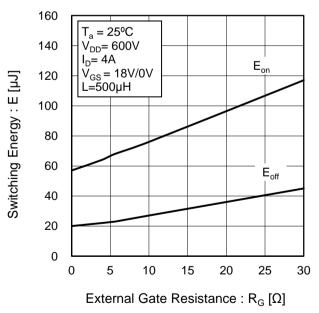
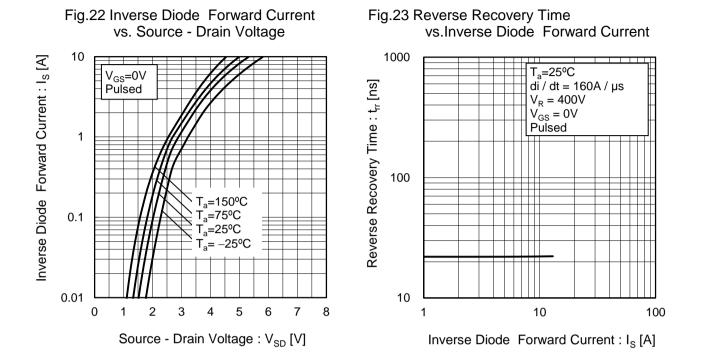


Fig.21 Typical Switching Loss vs. External Gate Resistance









Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

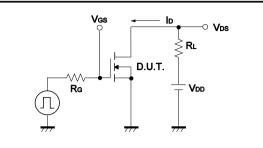


Fig.2-1 Gate Charge Measurement Circuit

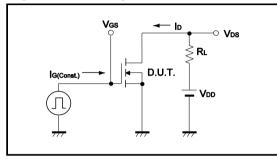


Fig.3-1 Switching Energy Measurement Circuit

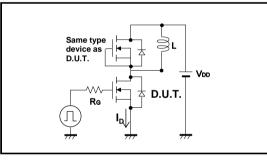
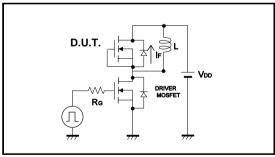
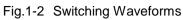


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform





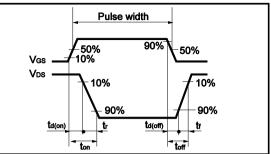


Fig.2-2 Gate Charge Waveform

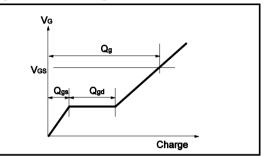
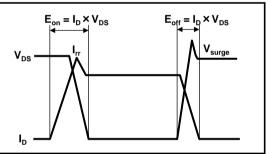
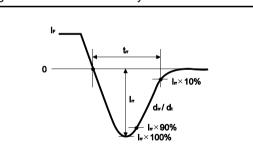


Fig.3-2 Switching Waveforms







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